

# INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(PTO-1449)

 ATTY. DOCKET NO.  
60188-575

 SERIAL NO.  
Continuation of Appl. No.  
10/107,334

 APPLICANT  
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 FILING DATE  
November 07, 2003

 GROUP  
1775

## U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s) (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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